

TPIC5401 H-BRIDGE GATE-PROTECTED POWER DMOS ARRAY

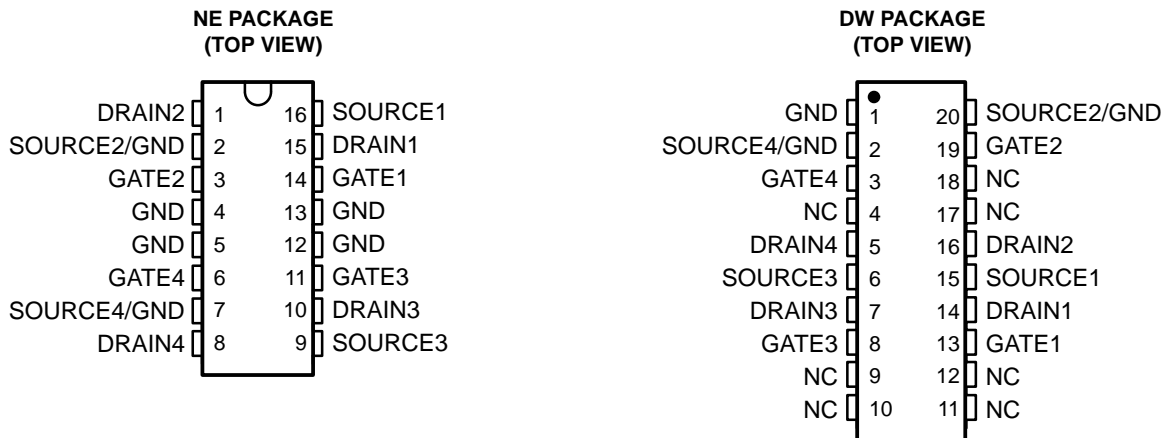
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- Low $r_{DS(on)}$. . . 0.3 Ω Typ
- High Voltage Output . . . 60 V
- Extended ESD Capability . . . 4000 V
- Pulsed Current . . . 10 A Per Channel
- Fast Commutation Speed

description

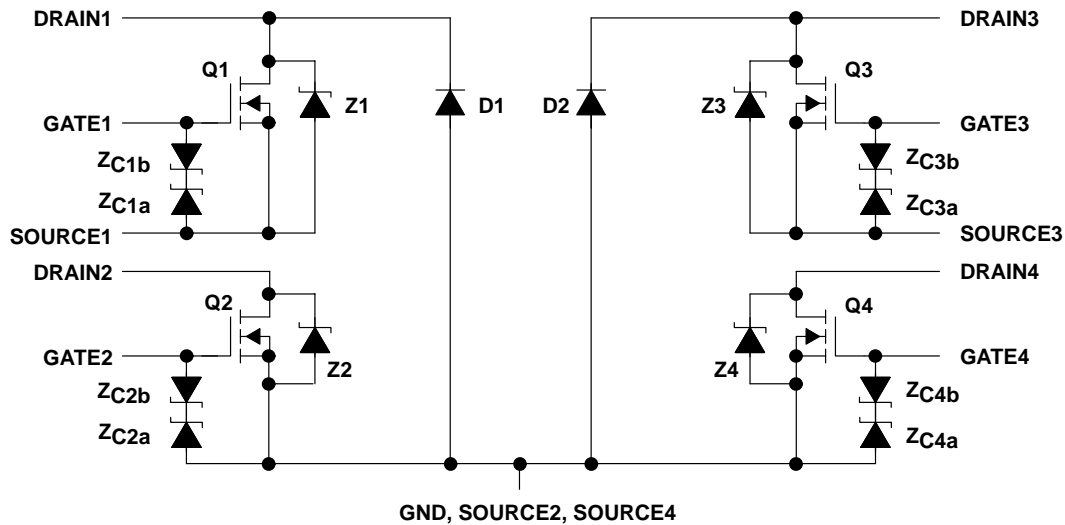
The TPIC5401 is a monolithic gate-protected power DMOS array that consists of four N-channel enhancement-mode DMOS transistors, two of which are configured with a common source. Each transistor features integrated high-current zener diodes (Z_{CXa} and Z_{CXb}) to prevent gate damage in the event that an overstress condition occurs. These zener diodes also provide up to 4000 V of ESD protection when tested using the human-body model of a 100-pF capacitor in series with a 1.5-k Ω resistor.

The TPIC5401 is offered in a 16-pin thermally enhanced dual-in-line (NE) package and a 20-pin wide-body surface-mount (DW) package and is characterized for operation over the case temperature range of -40°C to 125°C .



NC – No internal connection

schematic



NOTE: For correct operation, no terminal pin may be taken below GND.

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absolute maximum ratings over operating case temperature range (unless otherwise noted)†

Drain-to-source voltage, V_{DS}	60 V
Source-to-GND voltage (Q1, Q3)	100 V
Drain-to-GND voltage (Q1, Q3)	100 V
Drain-to-GND voltage (Q2, Q4)	60 V
Gate-to-source voltage range, V_{GS}	-9 V to 18 V
Continuous drain current, each output, $T_C = 25^\circ\text{C}$: DW package	1.7 A
NE package	2 A
Continuous source-to-drain diode current, $T_C = 25^\circ\text{C}$	2 A
Pulsed drain current, each output, I_{max} , $T_C = 25^\circ\text{C}$ (see Note 1 and Figure 15)	10 A
Continuous gate-to-source zener-diode current, $T_C = 25^\circ\text{C}$	± 50 mA
Pulsed gate-to-source zener-diode current, $T_C = 25^\circ\text{C}$	± 500 mA
Single-pulse avalanche energy, E_{AS} , $T_C = 25^\circ\text{C}$ (see Figures 4, 15, and 16)	21 mJ
Continuous total dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T_J	-40°C to 150°C
Operating case temperature range, T_C	-40°C to 125°C
Storage temperature range,	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Pulse duration = 10 ms, duty cycle = 2%

DISSIPATION RATING TABLE

PACKAGE	$T_C \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_C = 25^\circ\text{C}$	$T_C = 125^\circ\text{C}$ POWER RATING
DW	1389 mW	11.1 mW/ $^\circ\text{C}$	279 mW
NE	2075 mW	16.6 mW/ $^\circ\text{C}$	415 mW



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electrical characteristics, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$	Drain-to-source breakdown voltage	$I_D = 250 \mu\text{A}$,	$V_{GS} = 0$	60			V
$V_{GS(th)}$	Gate-to-source threshold voltage	$I_D = 1 \text{ mA}$, See Figure 5	$V_{DS} = V_{GS}$,	1.5	1.85	2.2	V
$V_{(BR)GS}$	Gate-to-source breakdown voltage	$I_{GS} = 250 \mu\text{A}$		18			V
$V_{(BR)SG}$	Source-to-gate breakdown voltage	$I_{SG} = 250 \mu\text{A}$		9			V
$V_{(BR)}$	Reverse drain-to-GND breakdown voltage (across D1, D2)	Drain-to-GND current = $250 \mu\text{A}$		100			V
$V_{DS(on)}$	Drain-to-source on-state voltage	$I_D = 2 \text{ A}$, See Notes 2 and 3	$V_{GS} = 10 \text{ V}$,		0.6	0.7	V
$V_{F(SD)}$	Forward on-state voltage, source-to-drain	$I_S = 2 \text{ A}$, $V_{GS} = 0$ (Z1, Z2, Z3, Z4), See Notes 2 and 3 and Figure 12			1	1.2	V
V_F	Forward on-state voltage, GND-to-drain	$I_D = 2 \text{ A}$ (D1, D2), See Notes 2 and 3			7.5		V
I_{DSS}	Zero-gate-voltage drain current	$V_{DS} = 48 \text{ V}$, $V_{GS} = 0$	$T_C = 25^\circ\text{C}$	0.05	1		μA
			$T_C = 125^\circ\text{C}$	0.5	10		
I_{GSSF}	Forward-gate current, drain short circuited to source	$V_{GS} = 15 \text{ V}$,	$V_{DS} = 0$		20	200	nA
I_{GSSR}	Reverse-gate current, drain short circuited to source	$V_{SG} = 5 \text{ V}$,	$V_{DS} = 0$		10	100	nA
I_{lkg}	Leakage current, drain-to-GND	$V_{DGND} = 48 \text{ V}$	$T_C = 25^\circ\text{C}$	0.05	1		μA
			$T_C = 125^\circ\text{C}$	0.5	10		
$r_{DS(on)}$	Static drain-to-source on-state resistance	$V_{GS} = 10 \text{ V}$, $I_D = 2 \text{ A}$, See Notes 2 and 3 and Figures 6 and 7	$T_C = 25^\circ\text{C}$	0.3	0.35		Ω
			$T_C = 125^\circ\text{C}$	0.47	0.5		
g_{fs}	Forward transconductance	$V_{DS} = 15 \text{ V}$, See Notes 2 and 3 and Figure 9	$I_D = 1 \text{ A}$,	1.6	1.9		S
C_{iss}	Short-circuit input capacitance, common source				220	275	pF
C_{oss}	Short-circuit output capacitance, common source	$V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$,	$V_{GS} = 0$, See Figure 11		120	150	
C_{rss}	Short-circuit reverse-transfer capacitance, common source				100	125	

- NOTES: 2. Technique should limit $T_J - T_C$ to 10°C maximum.
3. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

source-to-drain and GND-to-drain diode characteristics, $T_C = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{rr}	Reverse-recovery time	$I_S = 1 \text{ A}$, $V_{GS} = 0$, See Figures 1 and 14	$V_{DS} = 48 \text{ V}$, $di/dt = 100 \text{ A}/\mu\text{s}$,	Z1 and Z3	120		ns
				Z2 and Z4	280		
				D1 and D2	260		
Q_{RR}	Total diode charge			Z1 and Z3	0.12		μC
				Z2 and Z4	0.9		
				D1 and D2	2.2		



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resistive-load switching characteristics, $T_C = 25^\circ\text{C}$

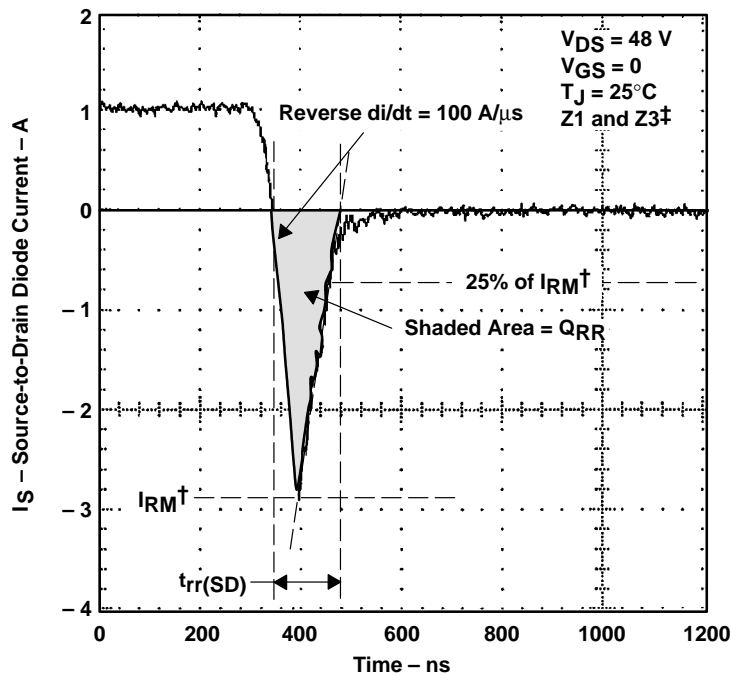
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(on)}$ Turn-on delay time	$V_{DD} = 25\text{ V}$, $R_L = 25\ \Omega$, $t_{en} = 10\text{ ns}$, $t_{dis} = 10\text{ ns}$, See Figure 2		32	65	ns
$t_{d(off)}$ Turn-off delay time			40	80	
t_r Rise time			15	30	
t_f Fall time			25	50	
Q_g Total gate charge	$V_{DS} = 48\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 10\text{ V}$, See Figure 3		6.6	8	nC
$Q_{gs(th)}$ Threshold gate-to-source charge			0.8	1	
Q_{gd} Gate-to-drain charge			2.6	3.2	
L_d Internal drain inductance			5		nH
L_s Internal source inductance			5		
R_g Internal gate resistance			0.25		

thermal resistances

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$ Junction-to-ambient thermal resistance (see Note 4)	DW		90		$^\circ\text{C/W}$
	NE		60		
$R_{\theta JB}$ Junction-to-board thermal resistance	DW		53		
	NE		30		
$R_{\theta JP}$ Junction-to-pin thermal resistance	DW		30		
	NE		25		

NOTE 4: Package mounted on an FR4 printed-circuit board with no heatsink.

PARAMETER MEASUREMENT INFORMATION



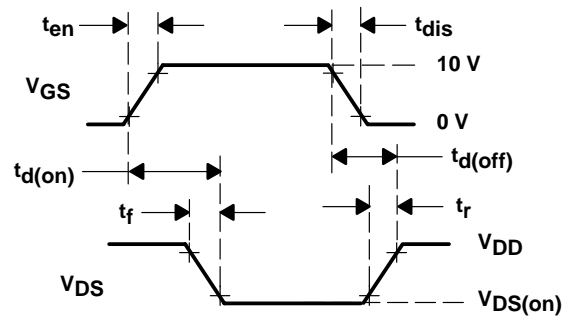
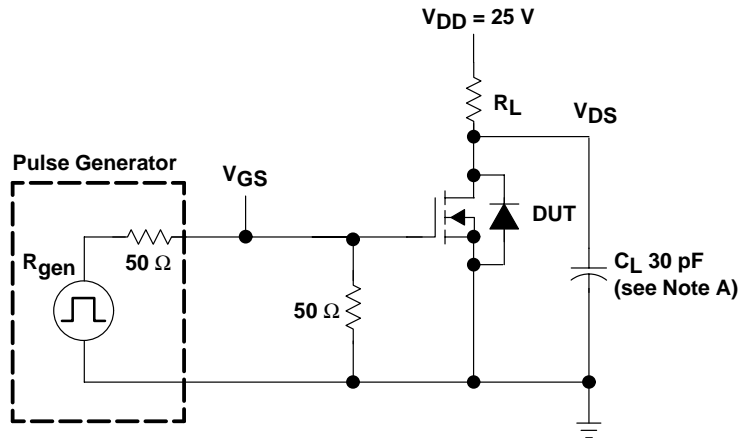
† I_{RM} = maximum recovery current

‡ The above waveform is representative of Z2, Z4, D1, and D2 in shape only.

Figure 1. Reverse-Recovery-Current Waveform of Source-to-Drain Diode



PARAMETER MEASUREMENT INFORMATION

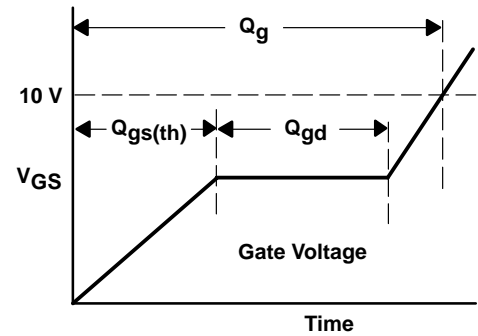
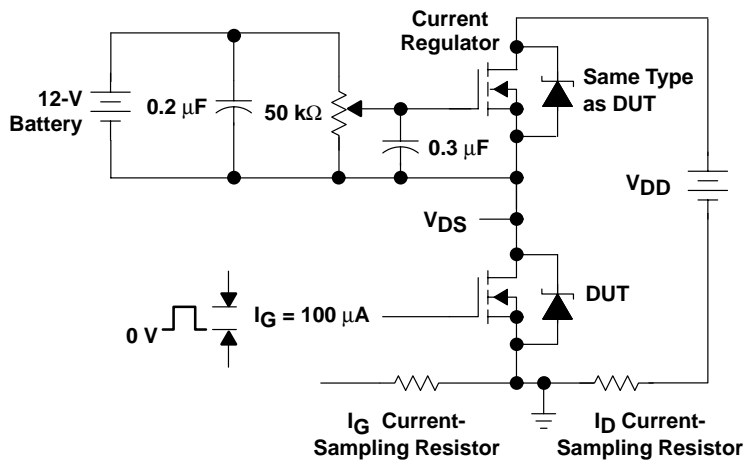


VOLTAGE WAVEFORMS

TEST CIRCUIT

NOTE A: C_L includes probe and jig capacitance.

Figure 2. Resistive-Switching Test Circuit and Voltage Waveforms



WAVEFORM

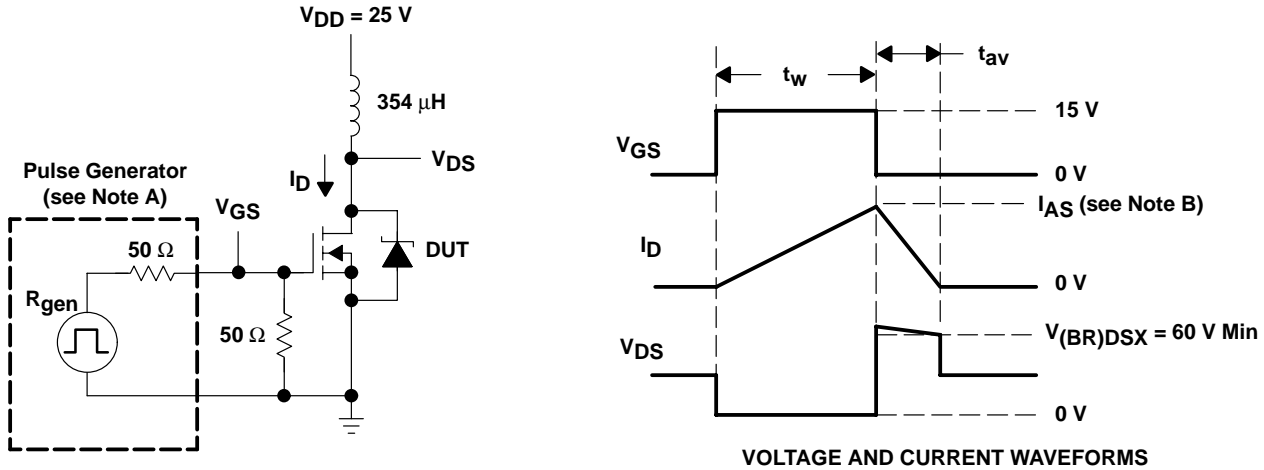
TEST CIRCUIT

Figure 3. Gate-Charge Test Circuit and Waveform

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PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

- NOTES: A. The pulse generator has the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_O = 50 \Omega$.
 B. Input pulse duration (t_w) is increased until peak current $I_{AS} = 10$ A.

Energy test level is defined as $E_{AS} = \frac{I_{AS} \times V_{(BR)DSX} \times t_{av}}{2} = 21$ mJ.

Figure 4. Single-Pulse Avalanche-Energy Test Circuit and Waveforms

TYPICAL CHARACTERISTICS

GATE-TO-SOURCE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

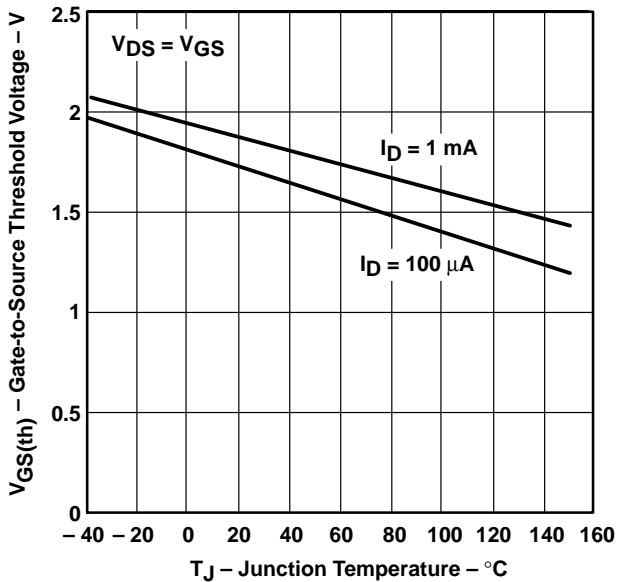


Figure 5

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE vs JUNCTION TEMPERATURE

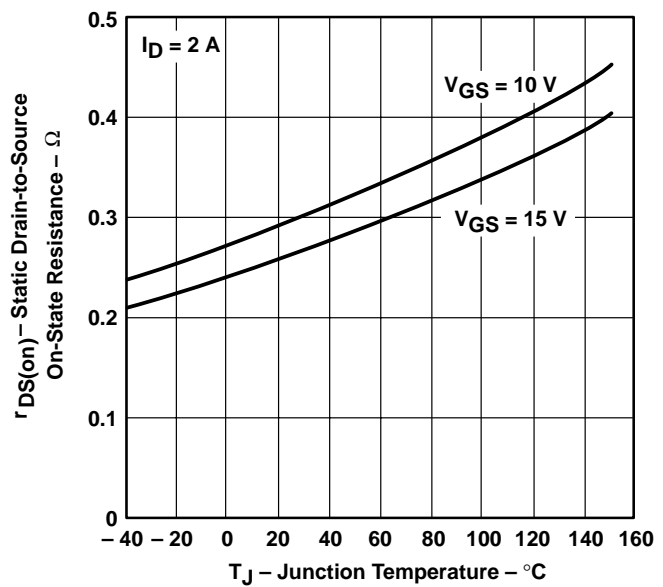


Figure 6



TYPICAL CHARACTERISTICS

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE
vs
DRAIN CURRENT

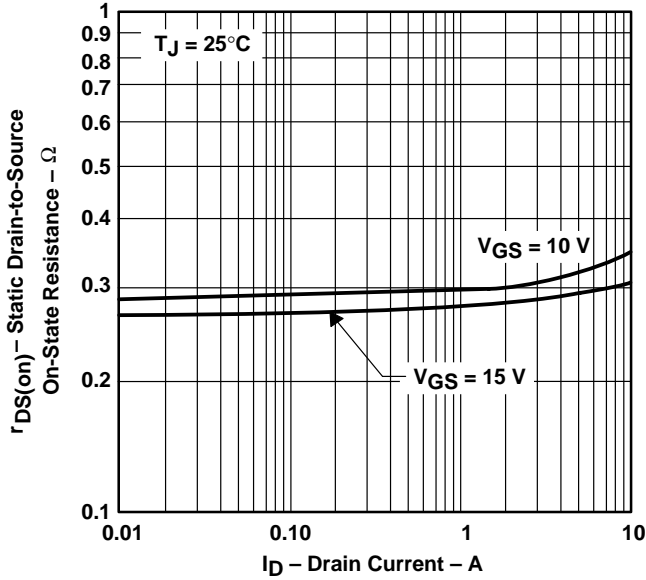


Figure 7

DRAIN CURRENT
vs
DRAIN-TO-SOURCE VOLTAGE

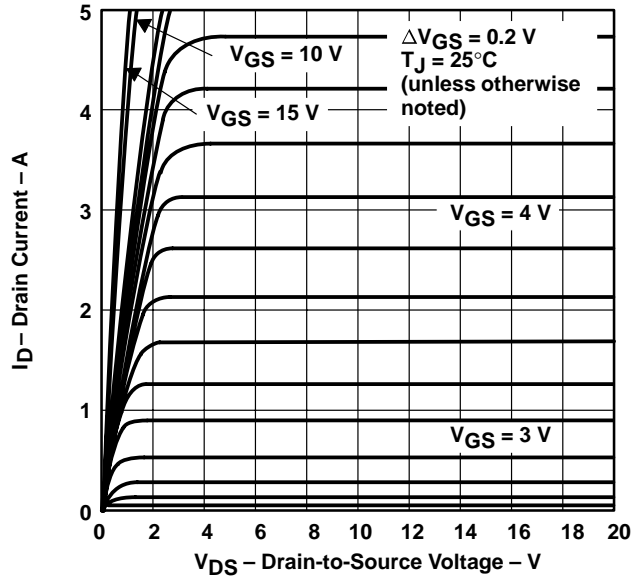


Figure 8

DISTRIBUTION OF
FORWARD TRANSCONDUCTANCE

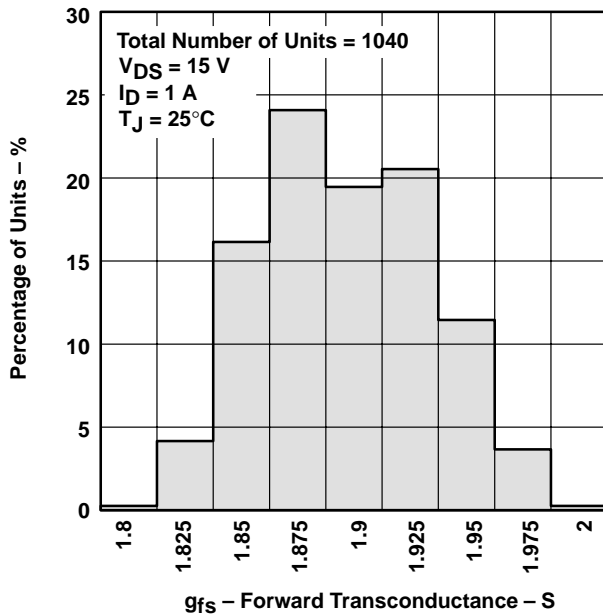


Figure 9

DRAIN CURRENT
vs
GATE-TO-SOURCE VOLTAGE

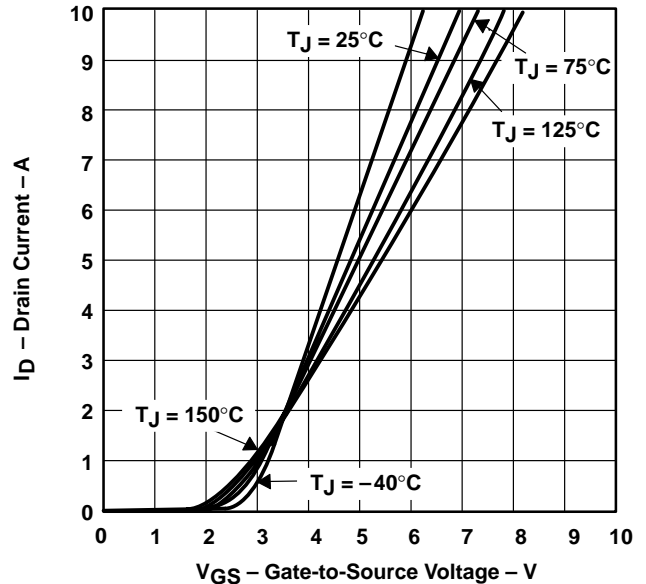


Figure 10

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TYPICAL CHARACTERISTICS

CAPACITANCE
vs
DRAIN-TO-SOURCE VOLTAGE

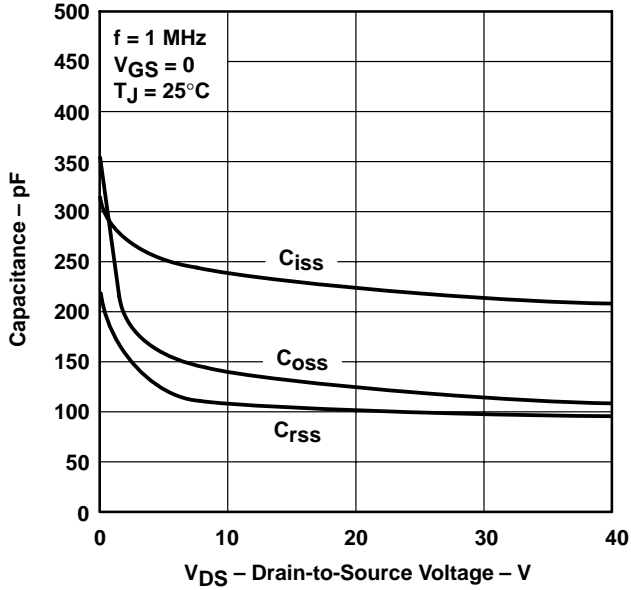


Figure 11

SOURCE-TO-DRAIN DIODE CURRENT
vs
SOURCE-TO-DRAIN VOLTAGE

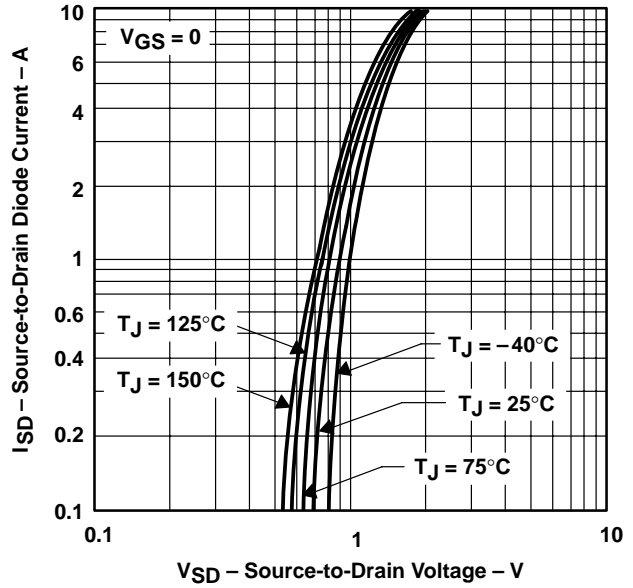


Figure 12

DRAIN-TO-SOURCE VOLTAGE
AND GATE-TO-SOURCE VOLTAGE
vs
GATE CHARGE

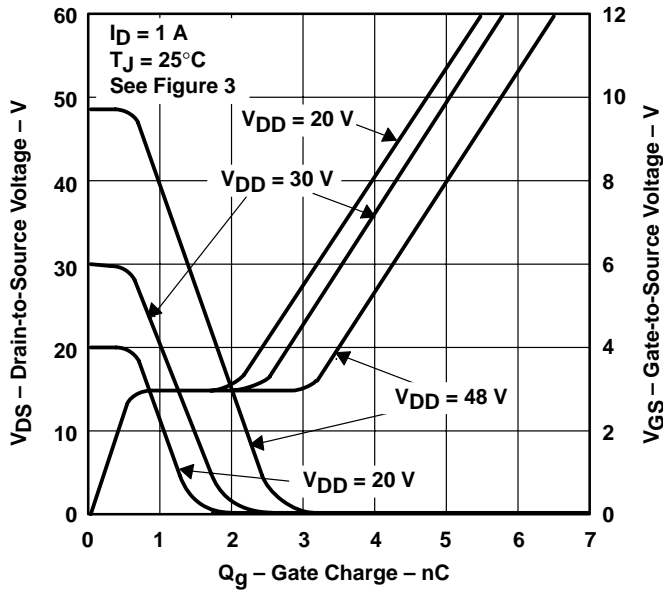


Figure 13

REVERSE-RECOVERY TIME
vs
REVERSE di/dt

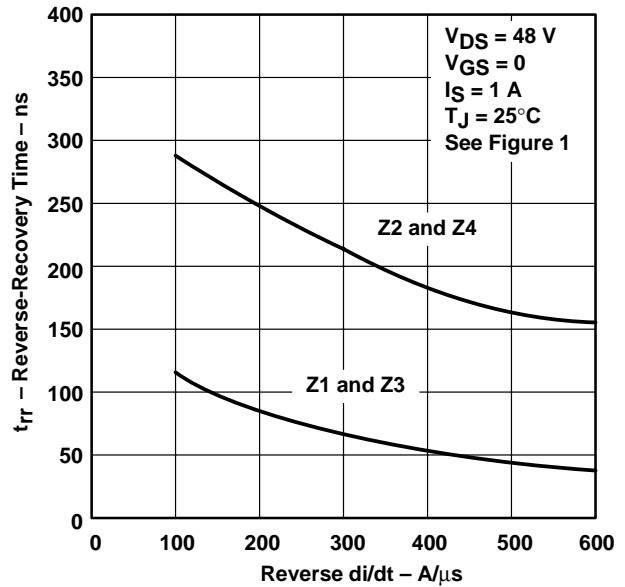
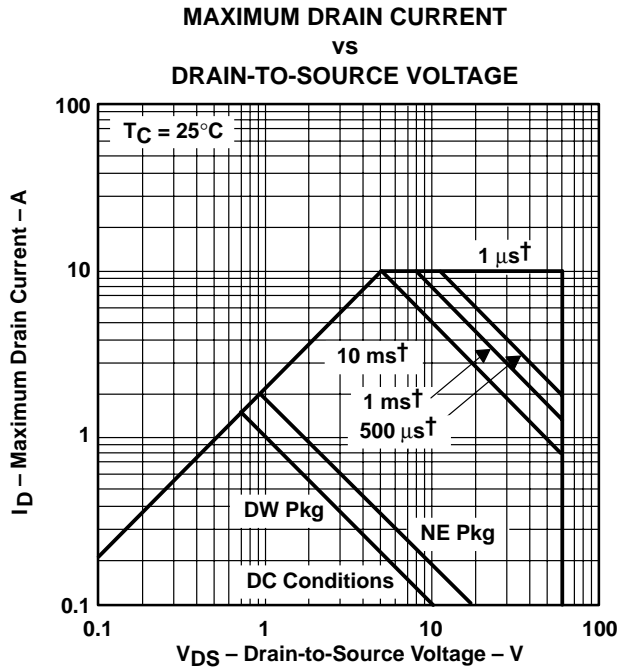


Figure 14



THERMAL INFORMATION



† Less than 2% duty cycle

Figure 15

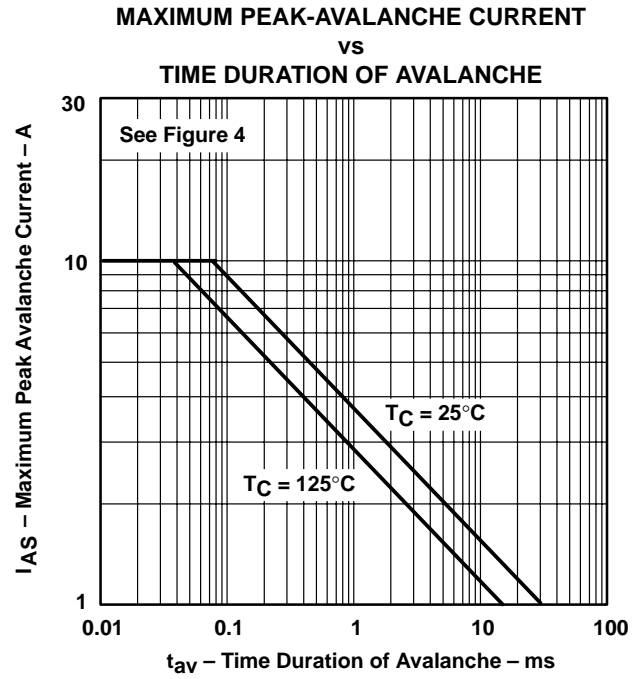


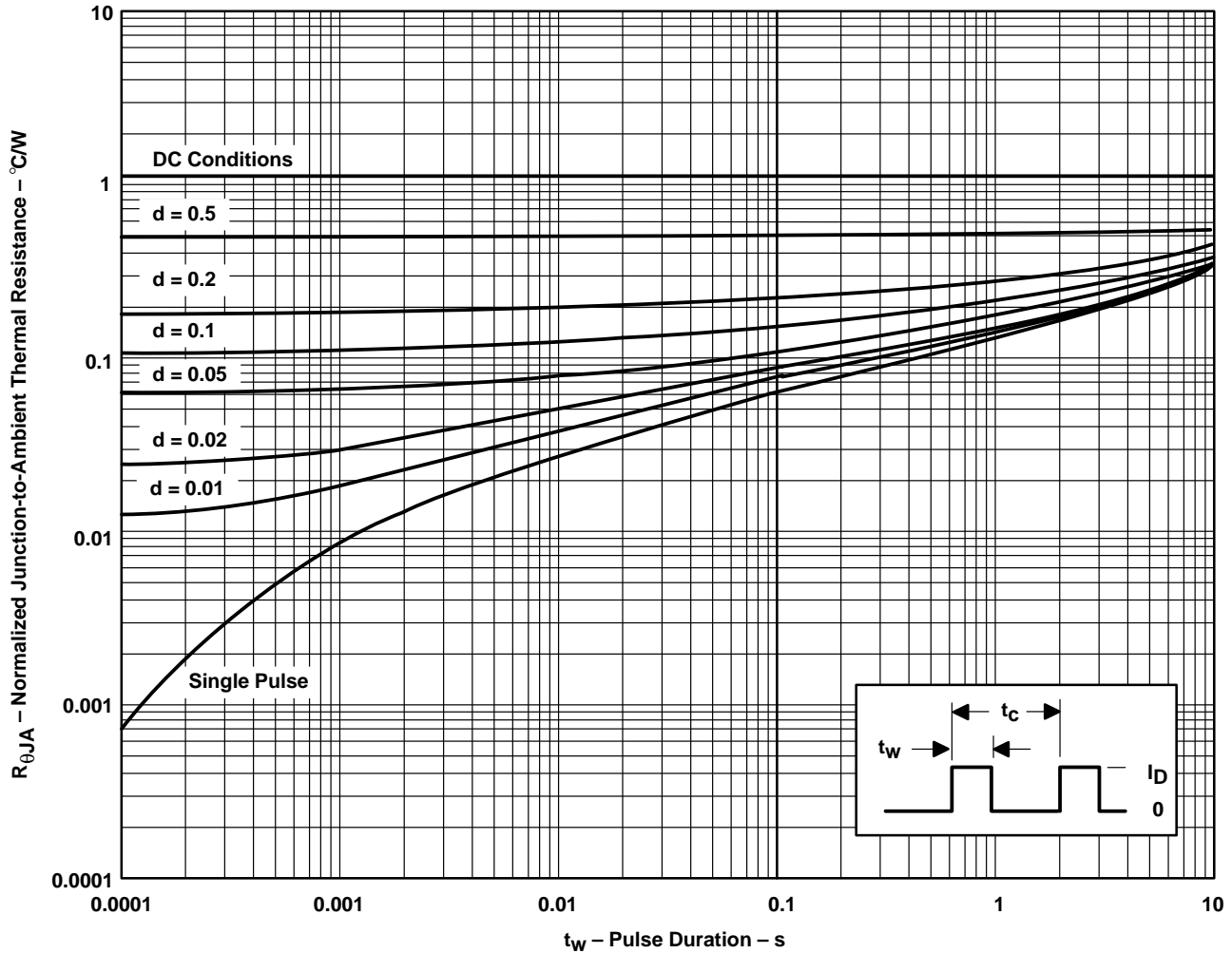
Figure 16

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THERMAL INFORMATION

NE PACKAGE†
NORMALIZED JUNCTION-TO-AMBIENT THERMAL RESISTANCE
VS
PULSE DURATION



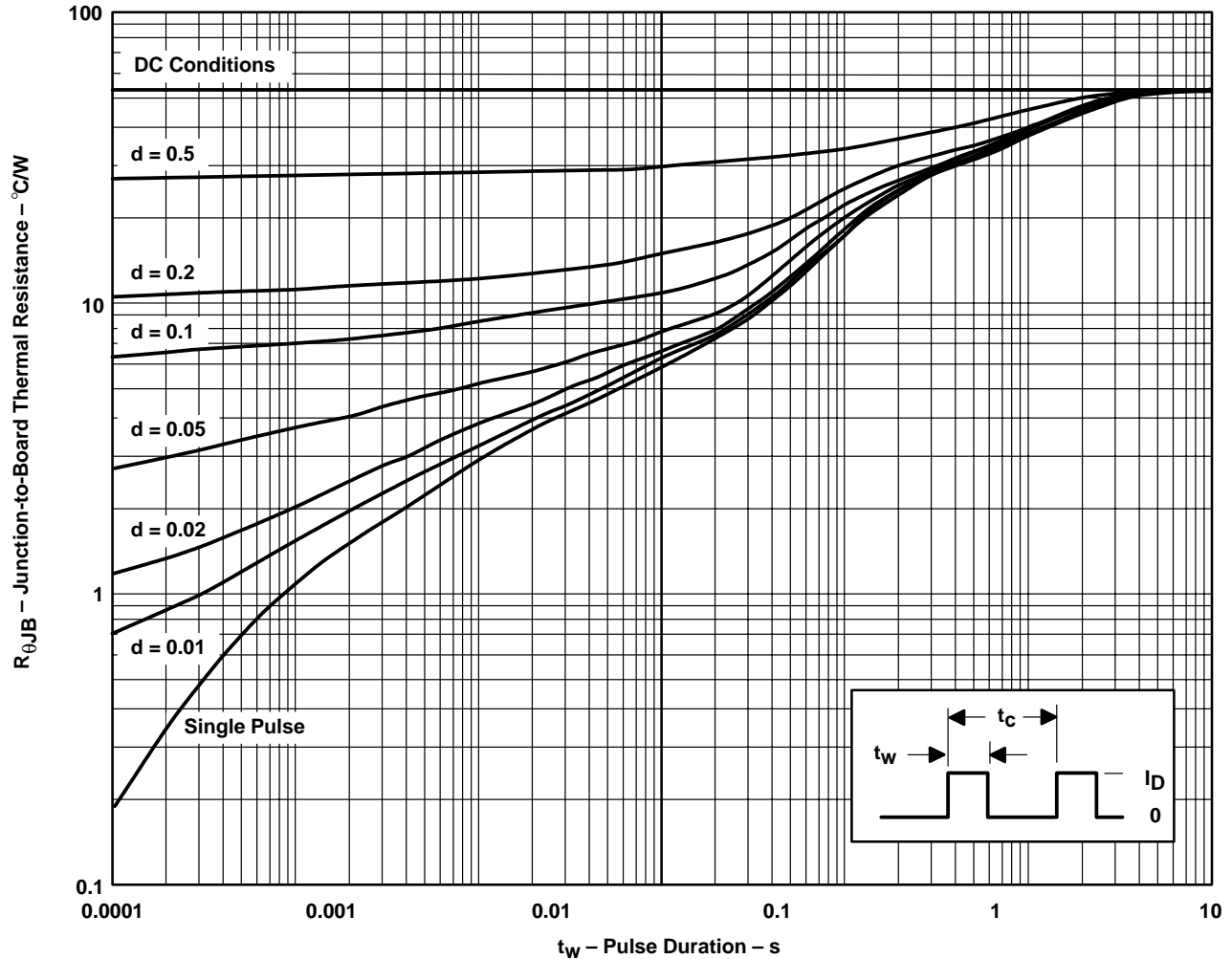
† Device mounted on FR4 printed-circuit board with no heatsink.

NOTE A: $Z_{\theta JA}(t) = r(t) R_{\theta JA}$
 t_w = pulse duration
 t_c = cycle time
 d = duty cycle = t_w/t_c

Figure 17

THERMAL INFORMATION

DW PACKAGE†
JUNCTION-TO-BOARD THERMAL RESISTANCE
VS
PULSE DURATION



† Device mounted on 24 in², 4-layer FR4 printed-circuit board with no heatsink.

NOTE B: $Z_{\theta JB}(t) = r(t) R_{\theta JB}$
 t_w = pulse duration
 t_c = cycle time
 d = duty cycle = t_w/t_c

Figure 18

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